

E4MS036120J2

Silicon Carbide Power MOSFET
Switching Optimized 1200 V 36 mΩ Automotive
N-Channel Enhancement Mode

Features

- Industry compatible drive voltage 15 V...18 V/-5 V...0 V
- Soft body diode with low Vds overshoot and ringing
- Low Rds(on) at high operating temperatures
- Improved device capacitances ratio (Ciss/Crss)
- High transient voltage robustness with improved lifetime
- Halogen free, RoHS compliant
- Automotive Qualified (AEC-Q101) and PPAP Capable

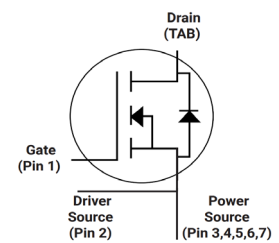
Benefits

- Higher efficiency with lower switching losses and EMI
- Faster switching operation enabling high power density
- Enables system level price performance optimization
- Reduction in system level cooling requirements

Typical Applications

- Motor Control
- EV On Board Battery Chargers (OBC)
- Automotive DC/DC Converters for EV/HEV

Package



Orderable Part number	Package type	Marking
E4MS036120J2-TR	TO-263-7XL	E4MS036120J2

Key Parameters

Parameter	Symbol	Min.	Typ.	Max	Unit	Conditions	Note
Drain - Source Voltage	V_{DS}			1200	V		
Maximum Gate - Source Voltage	$V_{GS(max)}$	-10		+23			Note 1
DC Continuous Drain Current	I_D			60	A	$V_{GS} = 18\text{ V}, T_c = 25\text{ }^\circ\text{C}, T_J \leq 175\text{ }^\circ\text{C}$	Note 2
				43		$V_{GS} = 18\text{ V}, T_c = 100\text{ }^\circ\text{C}, T_J \leq 175\text{ }^\circ\text{C}$	
Pulsed Drain Current	I_{DM}			193		t_{Pmax} limited by T_{Jmax} $V_{GS} = 18\text{ V}, T_c = 25\text{ }^\circ\text{C}$	
Power Dissipation	P_D			262	W	$T_c = 25\text{ }^\circ\text{C}, T_J = 175\text{ }^\circ\text{C}$	Note 3
Operating Junction and Storage Temperature	T_J, T_{stg}	-55		+175	$^\circ\text{C}$		
Solder Temperature	T_L			260			

Note (1): When applying IPC-9592B or OCP M-CRPS derating standards, a maximum Gate-Source voltage (V_{GS}) of +25 V is permissible.

Note (2): Current limit calculated by $I_{D(max)} = \sqrt{(P_D / R_{DS(typ)} (T_{J(max)} - T_{D(max)}))}$

Note (3): $P_D = (T_J - T_c) / R_{th(JC, max)}$


Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	2	2.6	3.9	V	$V_{DS} = V_{GS}, I_D = 7.6\text{ mA}$	Fig. 11
			2.0		V	$V_{DS} = V_{GS}, I_D = 7.6\text{ mA}, T_J = 175^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	μA	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	$V_{GS} = 18\text{ V}, V_{DS} = 0\text{ V}$	
$V_{GS(op)}$	Recommended Turn on Gate-Source Voltage		+15...+18		V		Refer to PRD-09634
	Recommended Turn off Gate-Source Voltage		-5...0				
$R_{DS(on)}$	Drain-Source On-State Resistance		36	47	m Ω	$V_{GS} = 18\text{ V}, I_D = 27.6\text{ A}$	Fig. 4, 5, 6
			66			$V_{GS} = 18\text{ V}, I_D = 27.6\text{ A}, T_J = 175^\circ\text{C}$	
			42			$V_{GS} = 15\text{ V}, I_D = 27.6\text{ A}$	
g_{fs}	Transconductance		20		S	$V_{DS} = 20\text{ V}, I_D = 27.6\text{ A}, T_J = 25^\circ\text{C}$	Fig. 7
			19			$V_{DS} = 20\text{ V}, I_D = 27.6\text{ A}, T_J = 175^\circ\text{C}$	
$R_{DS(on)Tempco}$	On resistance temperature coefficient		1.88			$V_{GS} = 18\text{ V}, I_D = 27.6\text{ A}$	Note 4
C_{iss}	Input Capacitance		2164		pF	$V_{GS} = 0\text{ V}, V_{DS} = 1000\text{ V}$ $f = 100\text{ kHz}$ $V_{AC} = 25\text{ mV}$	Fig. 17, 18
C_{oss}	Output Capacitance		72				
C_{rss}	Reverse Transfer Capacitance		3.2				
C_{iss}/C_{rss}	Capacitance Ratio		630				Note 5
E_{oss}	C_{oss} Stored Energy		46		μJ		Fig. 16
$C_{o(er)}$	Effective Output Capacitance (Energy Related)		106		pF	$V_{GS} = 0\text{ V}, V_{DS} = 0...800\text{ V}$	
$C_{o(tr)}$	Effective Output Capacitance (Time Related)		173				
E_{on}	Turn-On Switching Energy (Body Diode FWD)				μJ	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/18\text{ V},$ $I_D = 27.6\text{ A},$ $R_{G(ext)} = 2\text{ }\Omega, L_\sigma = 25\text{ nH}$	Fig. 26, 29, 31
	$T_J = 25^\circ\text{C}$		303				
E_{off}	Turn-Off Switching Energy (Body Diode FWD)				μJ	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/18\text{ V},$ $I_D = 27.6\text{ A},$ $R_{G(ext)} = 2\text{ }\Omega, L_\sigma = 25\text{ nH}$	Fig. 26, 29, 32
	$T_J = 175^\circ\text{C}$		393				
$t_{d(on)}$	Turn-On Delay Time		12		ns	$V_{DD} = 800\text{ V}, V_{GS} = -4\text{ V}/18\text{ V}$ $I_D = 27.6\text{ A}, R_{G(ext)} = 2\text{ }\Omega,$ Timing relative to V_{DS} Inductive load	Fig. 27, 28
t_r	Rise Time		3				
$t_{d(off)}$	Turn-Off Delay Time		29				
t_f	Fall Time		4				
$R_{G(int)}$	Internal Gate Resistance		2.4		Ω	$f = 1\text{ MHz}$	
Q_{gs}	Gate to Source Charge		24		nC	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/18\text{ V}$ $I_D = 27.6\text{ A}, T_J = 25^\circ\text{C}$ Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		23				
Q_g	Total Gate Charge		88				

Note (4): $R_{DS(on)Tempco}$ refers to $R_{DS(on)}$ at 175°C / $R_{DS(on)}$ at 25°C , E4MS 1200V product family value

Note (5): Capacitance ratio is a FOM for Partial turn-on immunity PRD-06933, E4MS 1200 V product family value

$Co(er)$, a lumped capacitance that gives the same stored energy as C_{oss} while V_{ds} is rising from 0 to 800 V

$Co(tr)$, a lumped capacitance that gives the same charging time as C_{oss} while V_{ds} is rising from 0 to 800 V



Reverse Diode Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	5.2		V	$V_{GS} = -4\text{ V}, I_{SD} = 13.8\text{ A}, T_J = 25^\circ\text{C}$	Fig. 8, 9, 10
		4.6		V	$V_{GS} = -4\text{ V}, I_{SD} = 13.8\text{ A}, T_J = 175^\circ\text{C}$	
I_S	Continuous Diode Forward Current		39	A	$V_{GS} = -4\text{ V}, T_c = 25^\circ\text{C}$	
I_{SM}	Diode Pulse Current		193	A	$V_{GS} = -4\text{ V}$, pulse width t_p limited by T_{jmax}	
t_{rr}	Reverse Recovery Time	11		ns	$V_{GS} = -4\text{ V}, I_S = 27.6\text{ A}, V_{SD} = 800\text{ V}$ $T_J = 175^\circ\text{C}, diF/dt = 7.6\text{ A/ns}$	
Q_{rr}	Reverse Recovery Charge	355		nC		
I_{RRM}	Peak Reverse Recovery Current	49		A		
E_{RR}	Reverse Recovery Energy			μJ	$V_{DS} = 800\text{ V}, I_D = 27.6\text{ A},$ $V_{GS} = -4\text{ V}/18\text{ V}, R_{G(on)} = 2\ \Omega, L_G = 25\text{ nH}$	
	$T_J = 25^\circ\text{C}$	29				
	$T_J = 175^\circ\text{C}$	35				

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.44	0.57	$^\circ\text{C/W}$		

Typical Performance

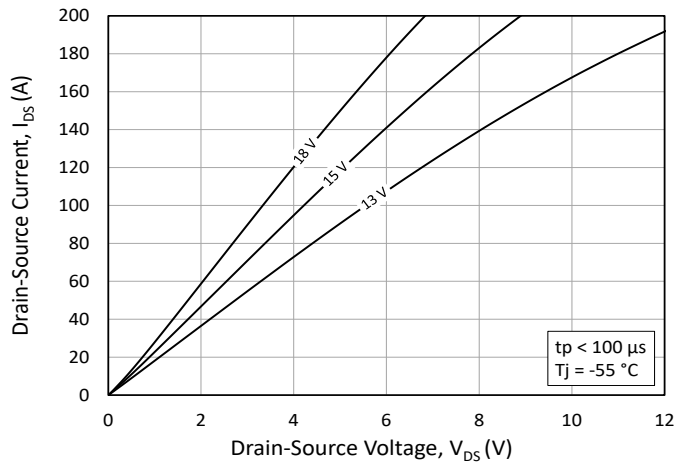


Figure 1. Output Characteristics $T_J = -55^{\circ}\text{C}$

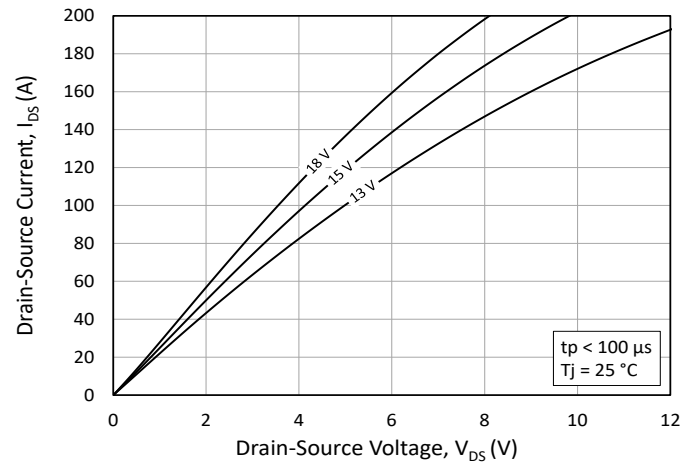


Figure 2. Output Characteristics $T_J = 25^{\circ}\text{C}$

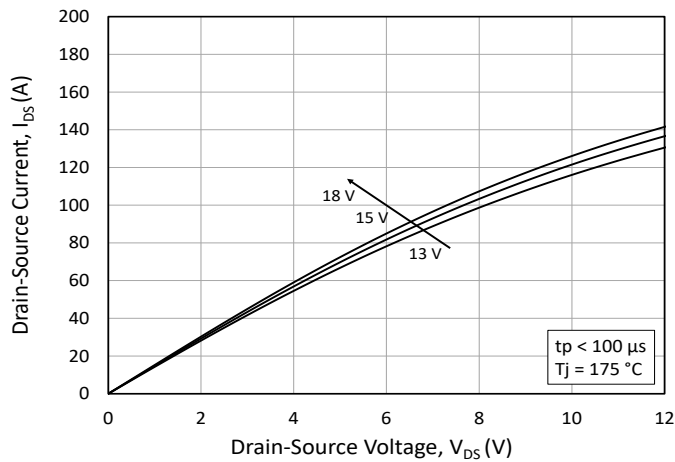


Figure 3. Output Characteristics $T_J = 175^{\circ}\text{C}$

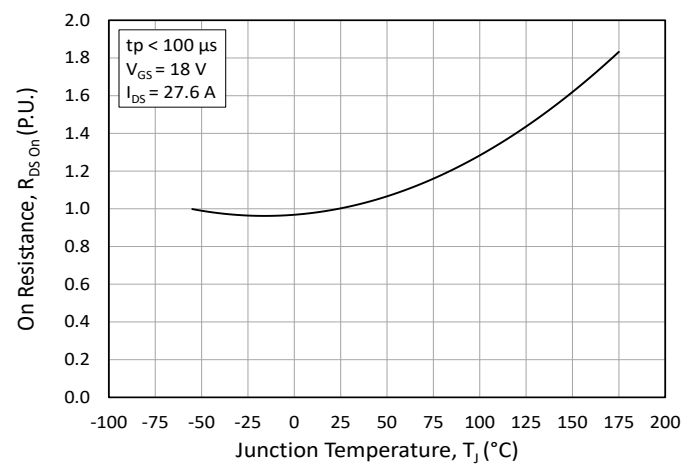


Figure 4. Normalized On-Resistance vs. Temperature

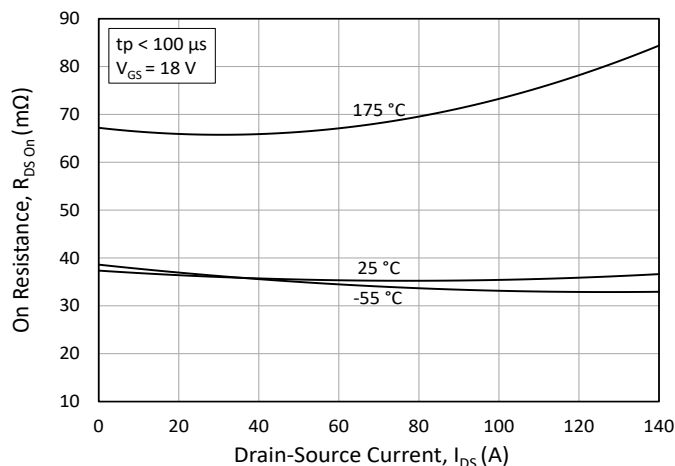


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

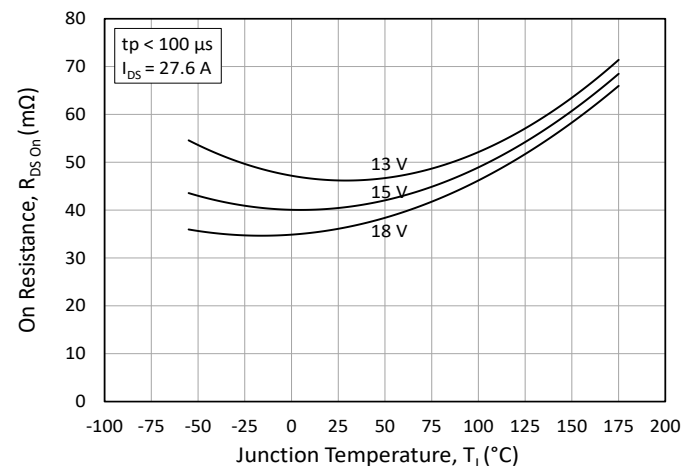


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance

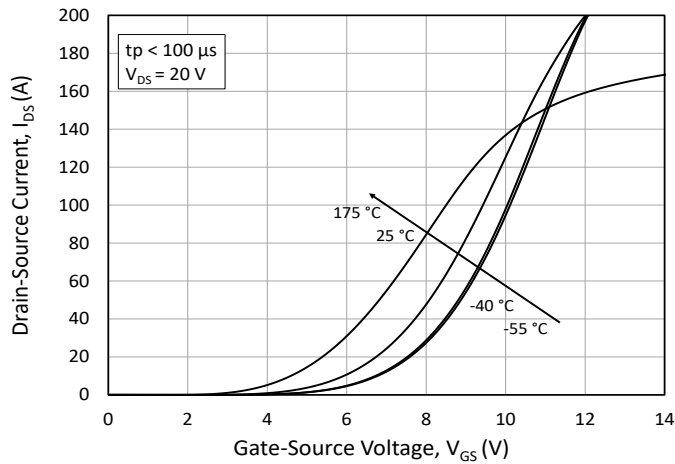


Figure 7. Transfer Characteristic for Various Junction Temperatures

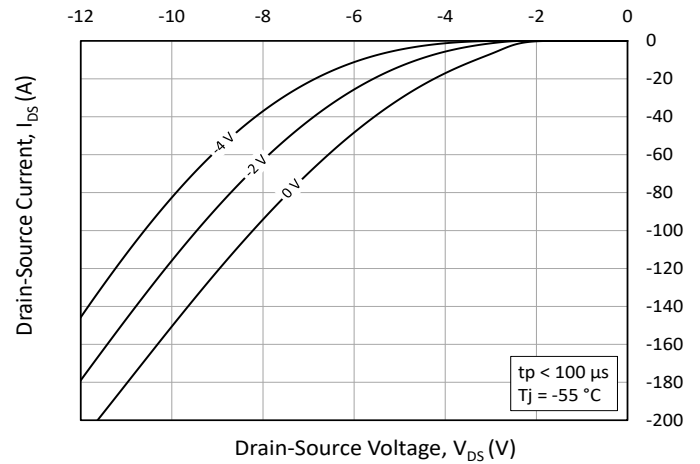


Figure 8. Body Diode Characteristic at -55 °C

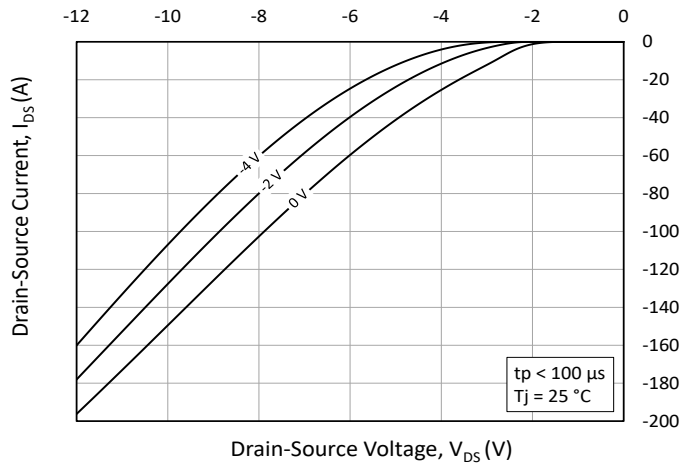


Figure 9. Body Diode Characteristic at 25 °C

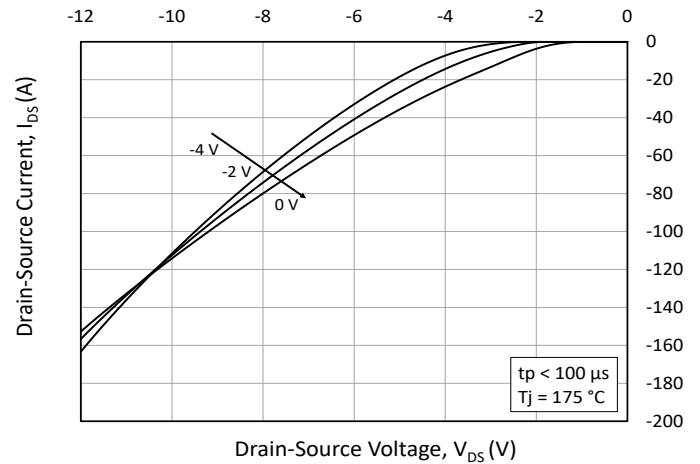


Figure 10. Body Diode Characteristic at 175 °C

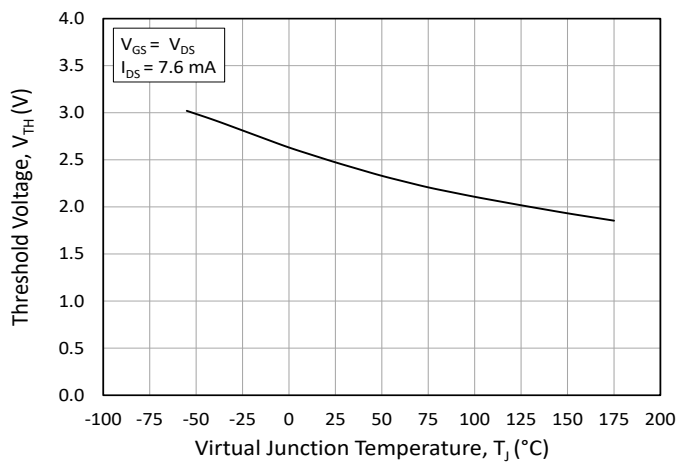


Figure 11. Threshold Voltage vs. Temperature

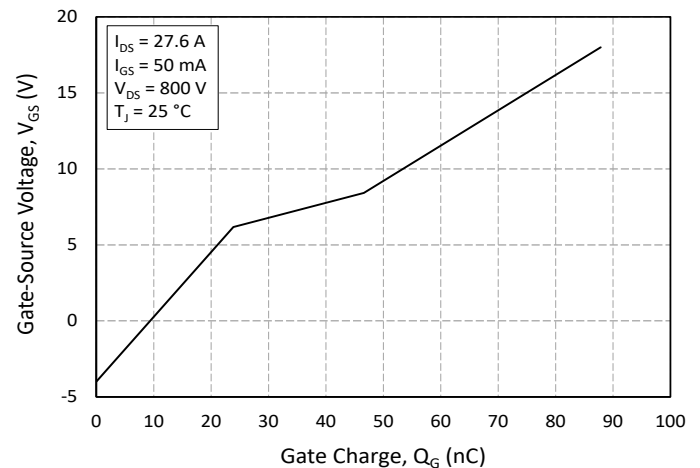


Figure 12. Gate Charge Characteristics

Typical Performance

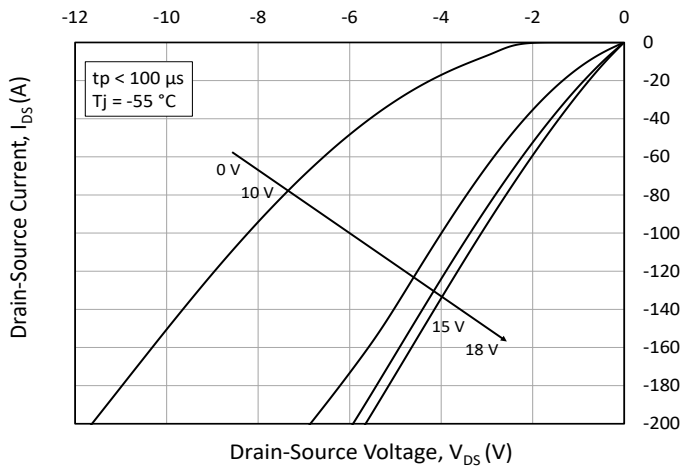


Figure 13. 3rd Quadrant Characteristic at -55°C

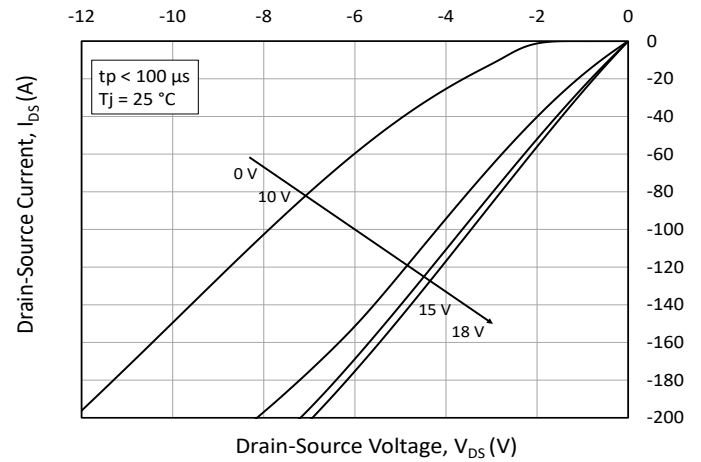


Figure 14. 3rd Quadrant Characteristic at 25°C

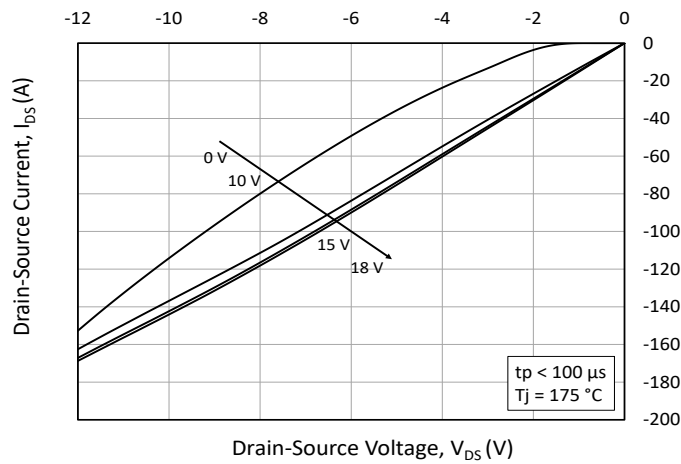


Figure 15. 3rd Quadrant Characteristic at 175°C

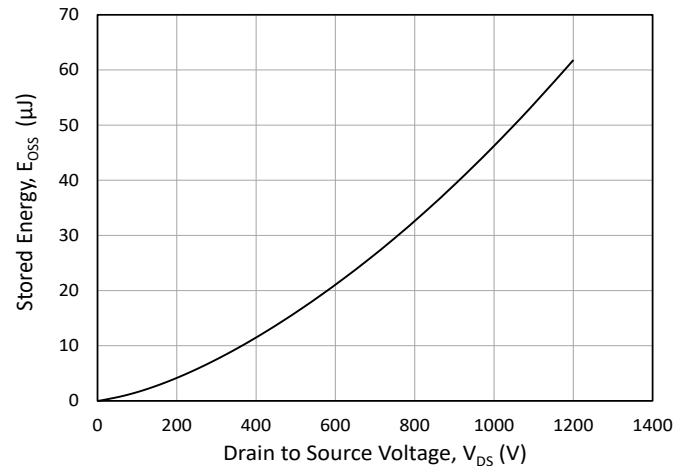


Figure 16. Output Capacitor Stored Energy

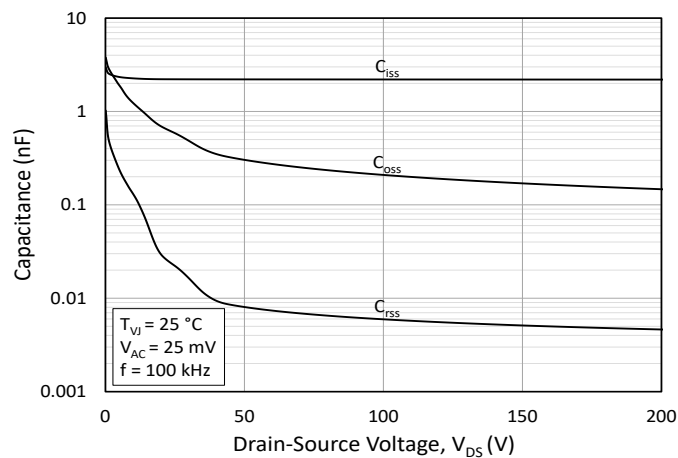


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200 V)

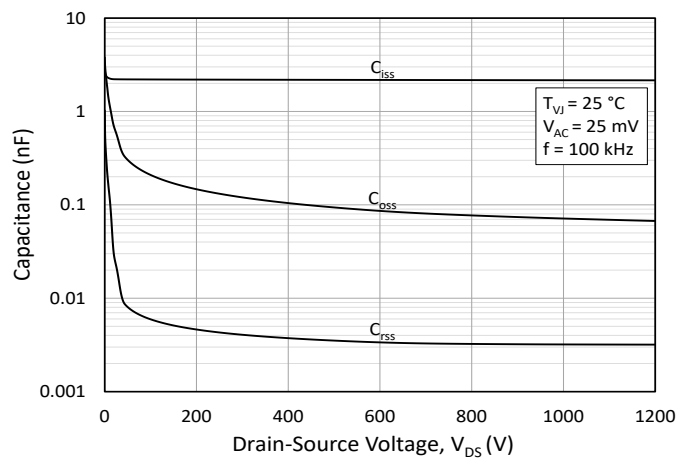


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1200 V)

Typical Performance

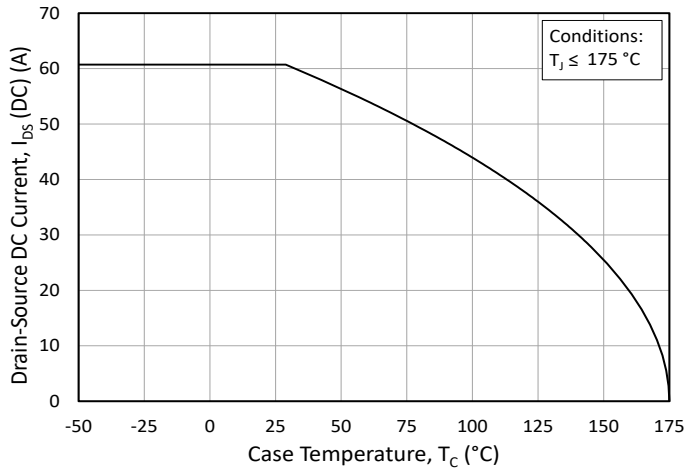


Figure 19. Continuous Drain Current Derating vs. Case Temperature

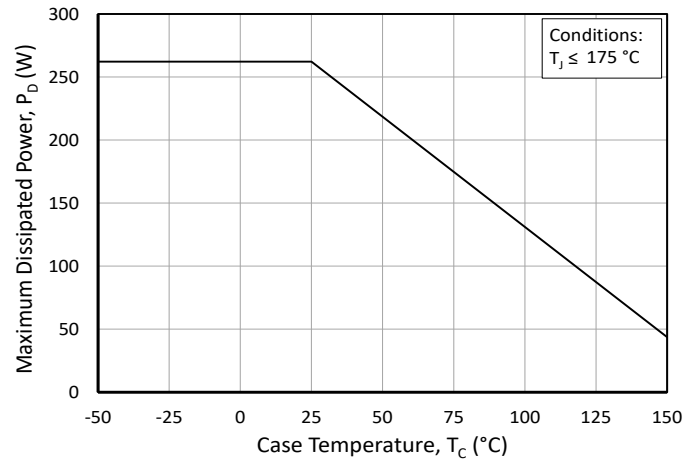


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

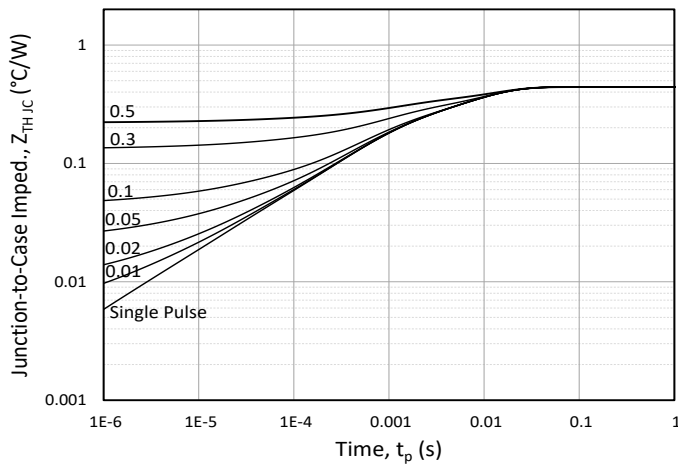


Figure 21. Transient Thermal Impedance (Junction - Case)

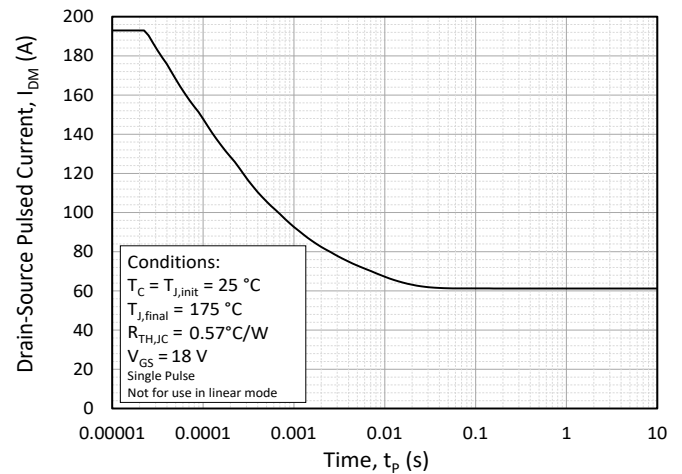


Figure 22. Safe Operating Area

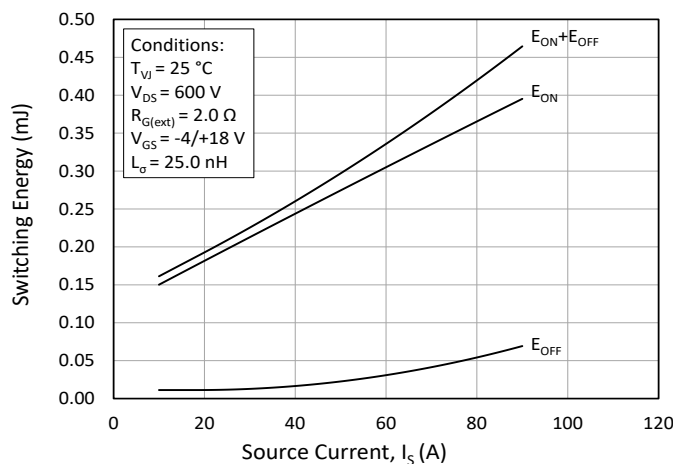


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 600 \text{ V}$)

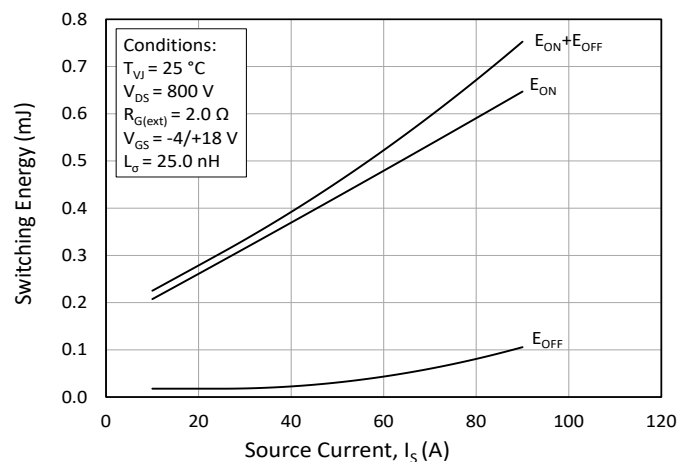


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 800 \text{ V}$)

Typical Performance

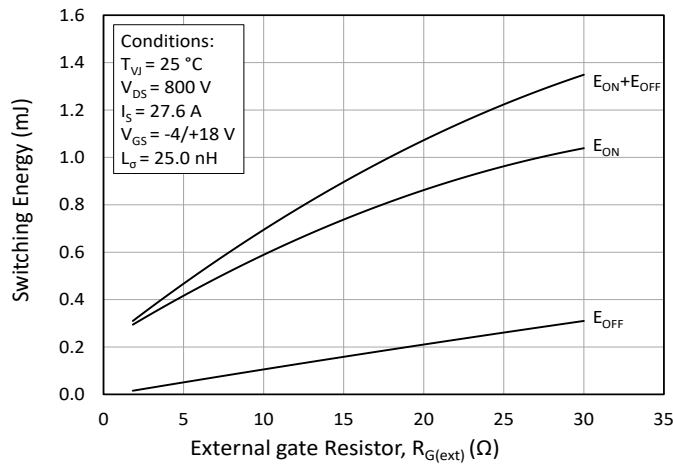
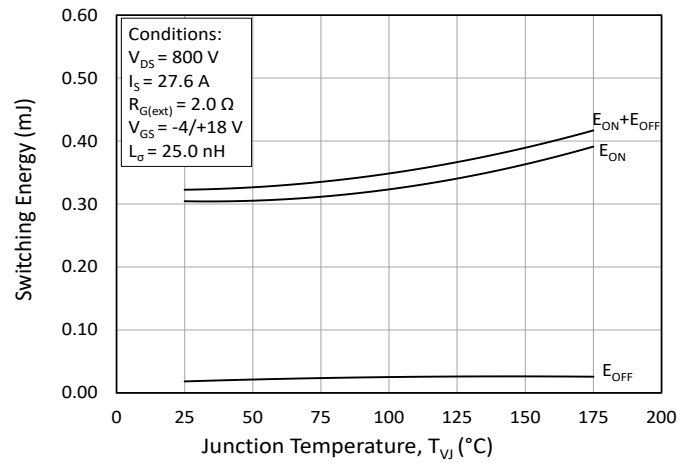
Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$ 

Figure 26. Clamped Inductive Switching Energy vs. Temperature

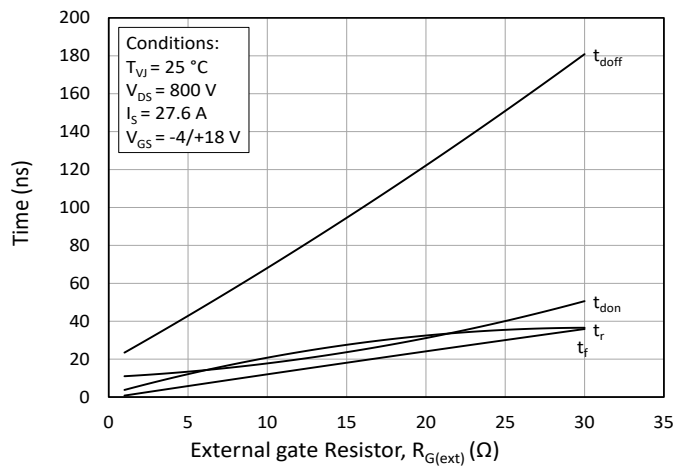
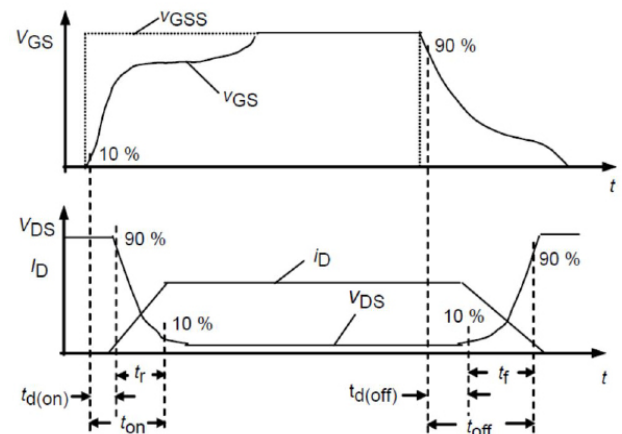
Figure 27. Switching Times vs. $R_{G(ext)}$ 

Figure 28. Switching Times Definition

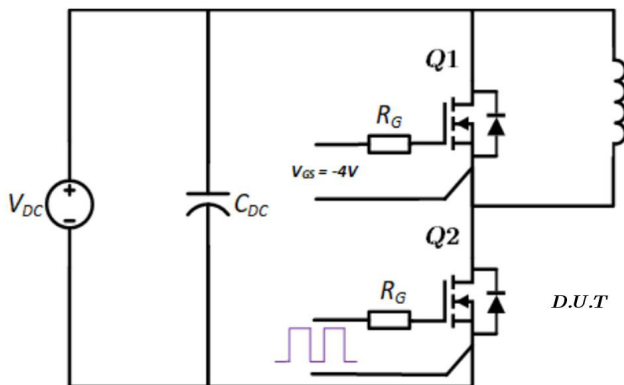


Figure 29. Clamped Inductive MOSFET Switching Waveform Test Circuit

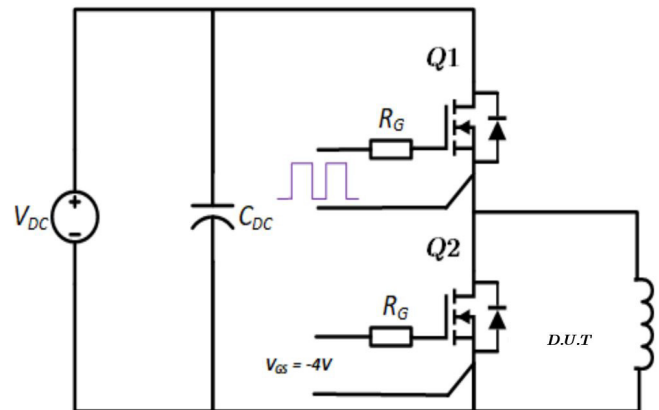
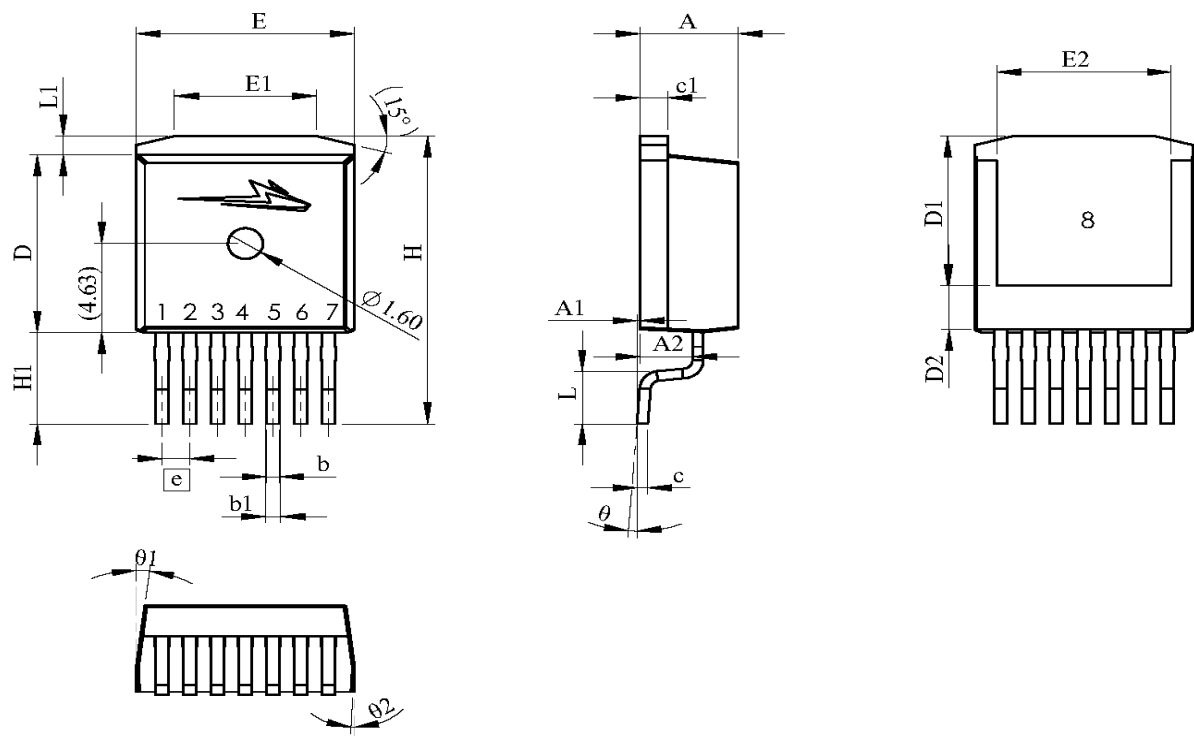


Figure 30. Clamped Inductive Body diode Switching Waveform Test Circuit

Package Dimensions



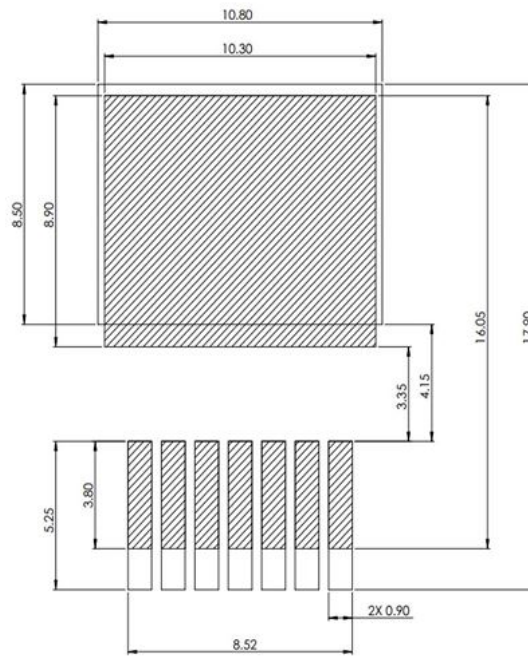
SYMBOL	MIN (mm)	MAX (mm)
A	4.30	4.70
A1	0.00	0.25
A2	2.20	2.60
b	0.52	0.72
b1	0.60	0.80
c	0.42	0.62
c1	1.07	1.47
D	9.05	9.45
D1	7.58	7.98
D2	2.05	2.45
E	9.80	10.20
E1	6.30	6.97
E2	7.80	8.20
e	1.27 BSC	
H	14.87	15.27
H1	4.55	4.95
L	2.48	2.88
L1	0.87	1.27
θ	0°	8°
θ1	4°	10°
θ2	0°	6°

1	GATE
2	KELVIN
3	SOURCE
4	
5	
6	
7	DRAIN
8	

- NOTE
- 1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.
 - 2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y 14.5M-1994.
 - 3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
 - 4. PACKAGE BURR FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS

Recommended Solder Pad Layout

All dimensions in mm



Revision History

Document Version	Date of release	Description of changes
1	November 2025	Initial release
2	January 2026	Addition of Note (1)
3	March 2026	Corrected the labels on Figures 8 and 9



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